



P-Channel 20-V (D-S) MOSFET

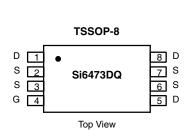
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 20	0.0125 at V _{GS} = - 4.5 V	- 9.5		
	0.016 at V _{GS} = - 2.5 V	- 8.5		
	0.0215 at V _{GS} = - 1.8 V	- 7.3		

FEATURES

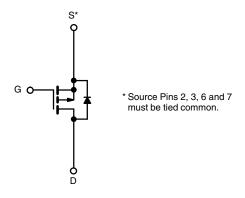
- Halogen-free
- TrenchFET® Power MOSFETs



ROHS



Ordering Information: Si6473DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 20		V	
Gate-Source Voltage		V _{GS}	± 8		V	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	- I _D	- 9.5	- 6.2	^	
	T _A = 70 °C		- 5.9	- 4.9		
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	- 30		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.5	- 0.95		
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	1.75	1.08	W	
	T _A = 70 °C		1.14	0.69] "	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifesture Investigat to Aughton 18	t ≤ 10 s	R _{thJA}	55	70	°C/W
Maximum Junction-to-Ambient ^a	Steady State		95	115	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	35	45	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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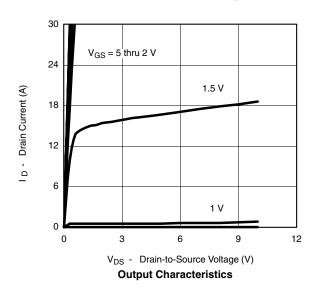
SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 0.45			٧		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 16 V, V _{GS} = 0 V			- 1			
		V _{DS} = - 16 V, V _{GS} = 0 V, T _J = 70 °C	V _{DS} = - 16 V, V _{GS} = 0 V, T _J = 70 °C			μΑ		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	20			Α		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -9.5 \text{ A}$		0.010	0.0125	16 Ω		
		V _{GS} = - 2.5 V, I _D = - 8.5 A		0.013	0.016			
		V _{GS} = - 1.8 V, I _D = - 7.5 A		0.0175	0.0215			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 9.5 A		45		S		
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.5 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.64	- 1.1	V		
Dynamic ^b								
Total Gate Charge	Q_g			47.5	70	nC		
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -9.5 \text{ A}$		7.6				
Gate-Drain Charge	Q_{gd}			7.6				
Turn-On Delay Time	t _{d(on)}			42	60			
Rise Time	t _r	V_{DD} = - 10 V, R_L = 15 Ω		33	50			
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, V_{GEN} = - 4.5 V, R_G = 6 Ω		220	330	ns		
Fall Time	t _f			95	140			
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = -1.5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		50	80			

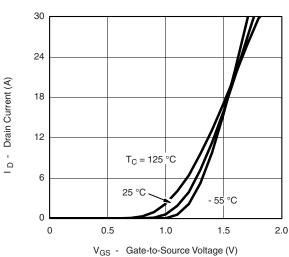
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



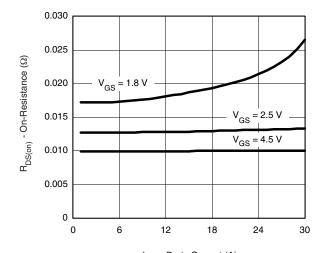


Transfer Characteristics



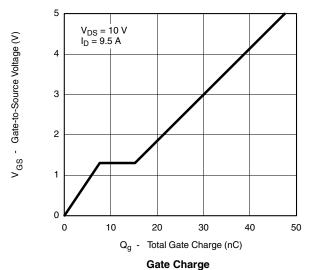


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

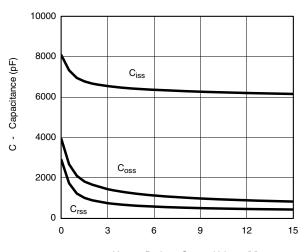


I_D - Drain Current (A)

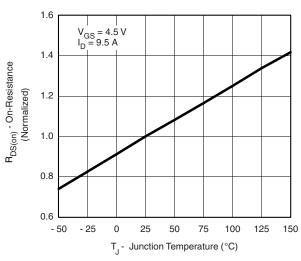
On-Resistance vs. Drain Current



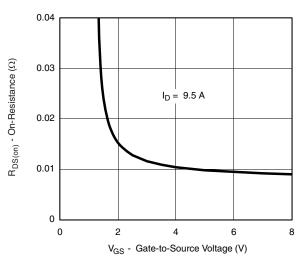
 $T_{J} = 150 \, ^{\circ}\text{C}$ $T_{J} = 25 \, ^{\circ}\text{C}$ $V_{SD} - \text{Source-to-Drain Voltage (V)}$ Source-Drain Diode Forward Voltage



V_{DS} - Drain-to-Source Voltage (V) **Capacitance**



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

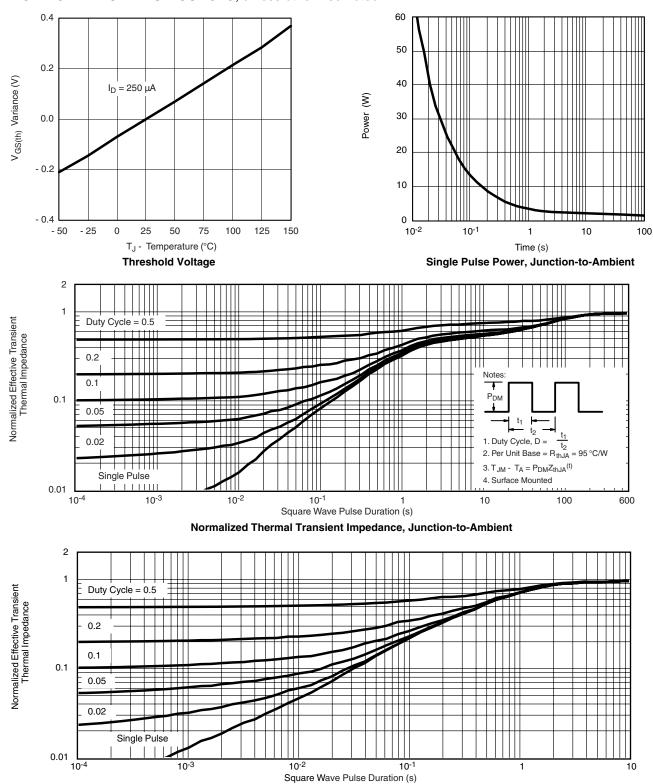
Source Current (A)

S

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?71164.



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